



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Silicon Carbide Thyristor

V_{FBM}	=	6500 V
$I_{T(AVM)}$	=	40 A
Q_{rr}	=	1.8 μ C

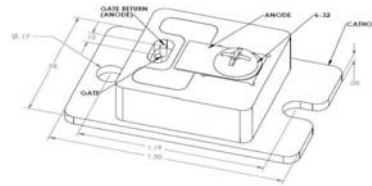
Features

- 6500 V Asymmetric SiC NPNP Thyristor
- 150 °C operating temperature
- Robust compact fully soldered package
- SOT-227 (ISOTOP) base plate form factor
- Fast turn on characteristics
- Lowest in class $Q_{rr}/I_{T(AVM)}$

Applications

- Grid Tied Solar Inverters
- Wind Power Inverters
- HVDC Power Conversion
- Utility Scale Power Conversion
- Trigger Circuits/Ignition Circuits

Package



Maximum Ratings

Parameter	Symbol	Conditions	Values	Unit
Repetitive peak forward voltage	V_{FBM}	$T_j = 25\text{ }^\circ\text{C}$	6500	V
Repetitive peak reverse voltage	V_{RBM}	$T_j = 25\text{ }^\circ\text{C}$	50	V
Maximum average on-state current	$I_{T(AVM)}$	$T_c \leq 120\text{ }^\circ\text{C}$	40	A
RMS on-state current	$I_{T(RMS)}$	$T_c \leq 120\text{ }^\circ\text{C}$	69	A
Non-repetitive peak on-state current	$I_{T,max}$	$T_c = 25\text{ }^\circ\text{C}$, $t_p = 2\text{ }\mu\text{s}$, $D = 0.1$	tbid	A
Power dissipation	P_{tot}	$T_c = 25\text{ }^\circ\text{C}$	595	W
Operating and storage temperature	T_j, T_{stg}		-55 to 150	$^\circ\text{C}$

Electrical Characteristics

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Maximum peak on state voltage	$V_{KA(ON)}$	$I_K = -40\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$ $I_K = -40\text{ A}$, $T_j = 150\text{ }^\circ\text{C}$		-4.30 -3.90		V
Anode-cathode threshold voltage	$V_{KA(TO)}$	$T_j = 25\text{ }^\circ\text{C}$ (150 °C)		-3.1(-2.8)		V
Anode-cathode slope resistance	R_{AK}	$T_j = 25\text{ }^\circ\text{C}$ (150 °C), $I_K = -40\text{ A}$		20(21)		m Ω
Leakage current	I_L	$V_{KA} = -6500\text{ V}$, $V_{GA} = 0\text{ V}$, $T_j = 25\text{ }^\circ\text{C}$ $V_{KA} = -6500\text{ V}$, $V_{GA} = 0\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$		15 30		μ A
Gate trigger current	I_{GT}	$T_j = 25\text{ }^\circ\text{C}$, $t_p = 10\text{ }\mu\text{s}$		-30		mA
Holding current	I_H	$T_j = 25\text{ }^\circ\text{C}$		780		mA
Rise time	t_R	$I_G = -3\text{ A}$, $V_{KA} = -2500\text{ V}$		200		ns
Delay time	t_D	$I_K = -40\text{ A}$, $T_j = 25\text{ }^\circ\text{C}$		40		ns
Reverse recovery charge	Q_{rr}			1.8		μ C
Recovered charge, 50% chord	Q_{ra}	$di/dt = 270\text{ A}/\mu\text{s}$, $I_K = -40\text{ A}$, $V_{KA} = 20\text{ V}$		0.6		μ C
Reverse recovery current	I_{rm}	$dV/dt(\text{re-app}) = -500\text{ V}/\mu\text{s}$, $T_j = 25\text{ }^\circ\text{C}$		11		A
Circuit commutated turn-off time	t_q			4.7		μs

Thermal Characteristics

Thermal resistance, junction - case	R_{thJC}	0.21	$^\circ\text{C}/\text{W}$
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Mechanical Properties

Mounting torque for base	M_b	Heat sink surface must be optically flat	1.5	Nm
Mounting torque for top	M_t		1.3	Nm
Weight	W_t		30	g

1. Considering worst case Z_{th} conditions

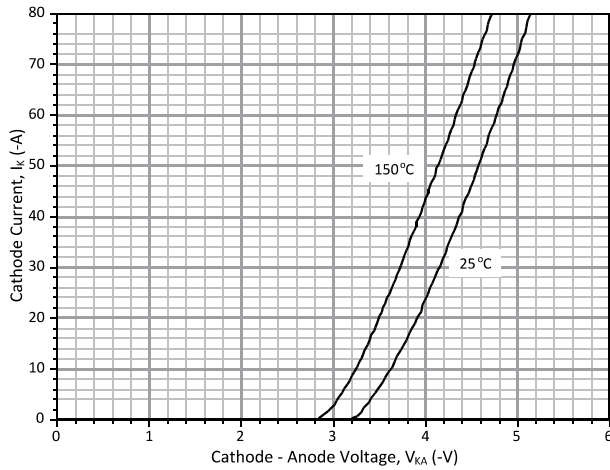


Figure 1: Typical On State Characteristics

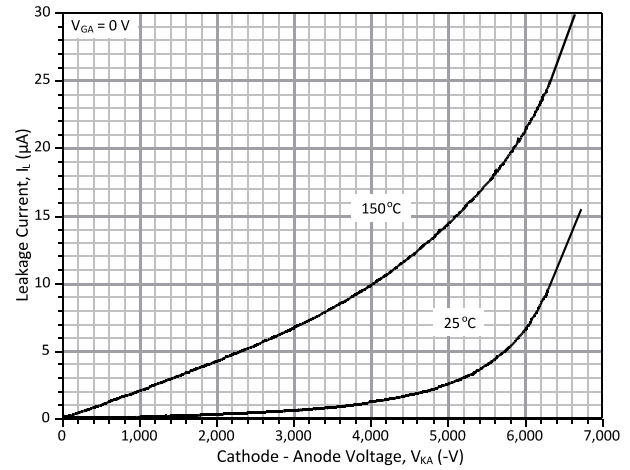


Figure 2: Typical Forward Blocking Characteristics

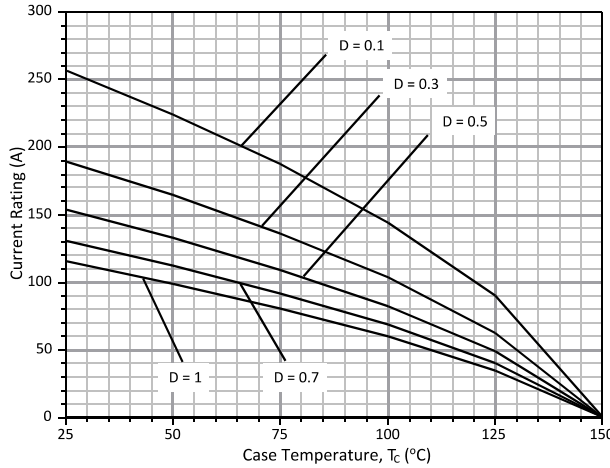


Figure 3: Typical Current Derating Curves ($D = t_p/T, t_p = 400 \mu s^1$)

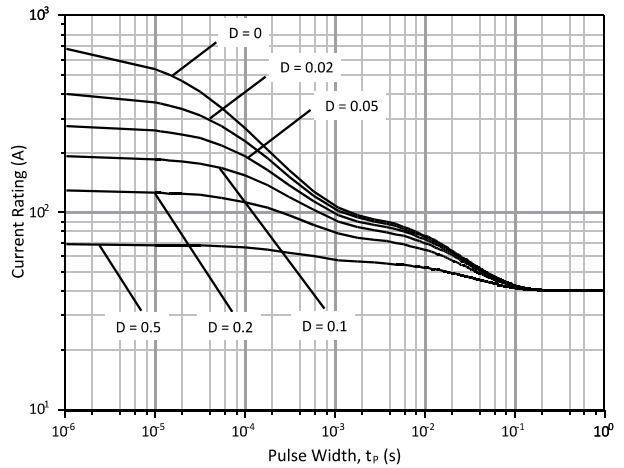


Figure 4: Typical Current Rating versus Pulse Duration Curves at $T_c = 120 \text{ }^\circ\text{C}$

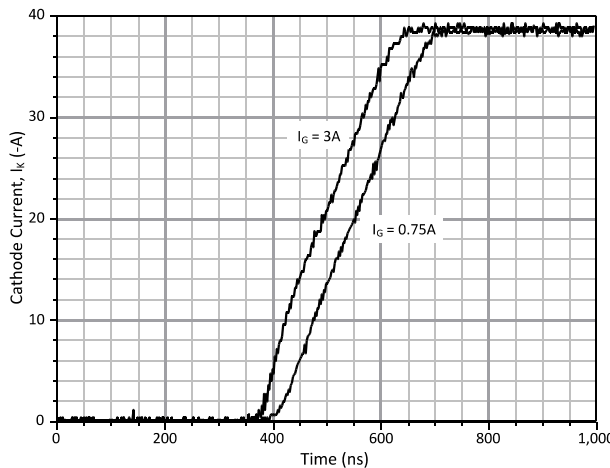


Figure 5: Typical Turn On Characteristics at 25 °C

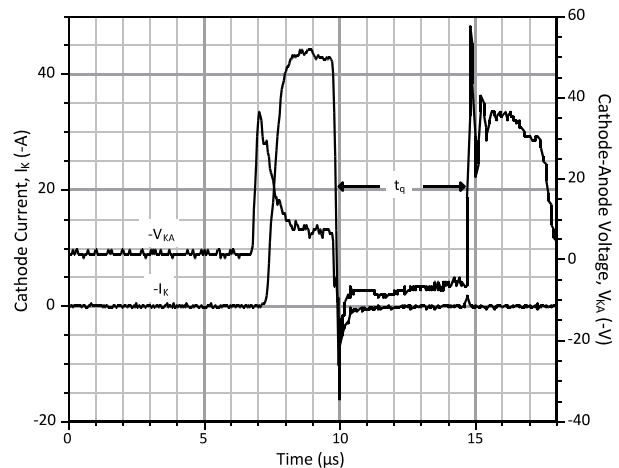


Figure 6: Typical Turn Off Characteristics at 25 °C

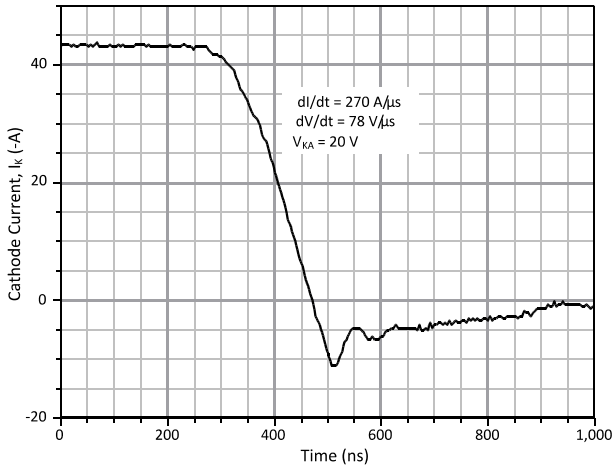


Figure 7: Typical Reverse Recovery Characteristics at 25 °C

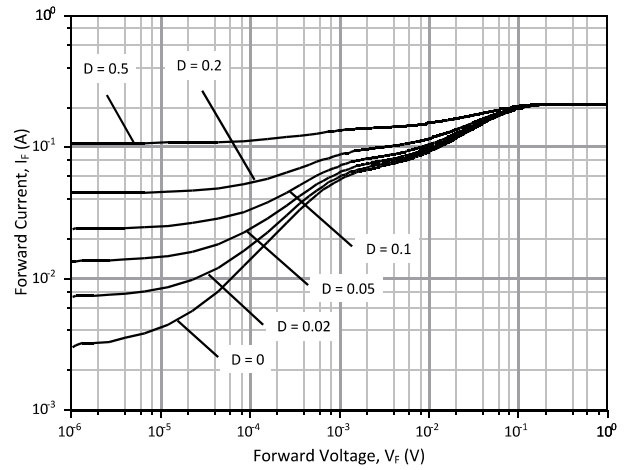


Figure 8: Typical Transient Thermal Impedance

Revision History

Date	Revision	Comments	Supersedes
2010/11/13	1	First generation release	

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